

ABSTRACT

POLYCRYSTALLINE SiC WAFER PRODUCING METHOD

There is provided a polycrystalline SiC wafer producing method. In this method, in a modified layer forming step for forming an interface for producing a polycrystalline SiC wafer from a polycrystalline SiC ingot, the formed interface is a surface formed by linking of modified layers formed in such a manner that an initial modified layer is formed through splitting of polycrystalline SiC into amorphous silicon and amorphous carbon at the light focus point of a pulse laser beam and then polycrystalline SiC splits into amorphous silicon and amorphous carbon at a position at which the power density is constant with absorption of the continuously-emitted pulse laser beam by amorphous carbon formed in advance.

(Figure 4A)